High Performance InGaAs p-i-n Photodiode

13PD150-TO

The 13PD150-TO, an InGaAs photodiode with a 150µm-diameter photosensitive region packaged in a TO-46 header, is intended for moderate-to-high speed applications. Efficient coupling to mulit-mode fiber in active device receptacles is enabled by the relatively large photosensitive area. Planar semiconductor design and dielectric passivation provide low noise performance. Reliability is assured by hermetic sealing and a 100% purge burn-in (200°C, 15 hours, V_r = 20V). Chips can also be attached and wire bonded to customer supplied or other specified packages. Headers are available with either a lensed or flat window cap.

Features

Planar Structure
Dielectric Passivation
100% Purge Burn-In
High Responsivity

Device Characteristics:

Parameters	Test Conditions	Min	Typ	Max	Units
Operating Voltage	-	-	-	-15	Volts
Dark Current	-5V	-	0.5	2.5	nA
Capacitance	-5V	-	1.50	2.25	pF
Responsivity	1300nm	0.7	0.85	-	A/W
Rise/Fall	-	-	-	2	ns

Absolute Maximum Ratings

Reverse Voltage	20 Volts
Forward Current	5 mA
Reverse Current	1 mA
Operating Temperature	-40°C to + 85°C
Storage Temperature	-40°C to + 85°C
Soldering Temperature	250°C

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